



## General Description

The IRFR130ATM use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable.

## General Features

$V_{DS} = 100V$   $I_D = 12A$

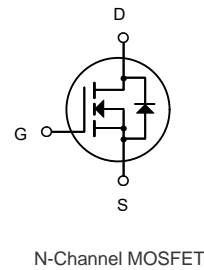
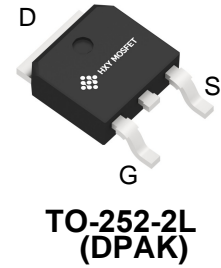
$R_{DS(ON)} < 120m\Omega @ V_{GS}=10V$

## Applications

Consumer electronic power supply

Motor control

Synchronous-rectification



## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR130ATM	TO-252-2L(DPAK)	HXY MOSFET	2500

## Absolute Maximum Ratings at $T_j=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain source voltage	100	V
V <sub>GS</sub>	Gate source voltage	±20	V
I <sub>D</sub>	Continuous drain current <sup>1)</sup>	12	A
I <sub>D, pulse</sub>	Pulsed drain current <sup>2)</sup>	24	A
P <sub>D</sub>	Power dissipation <sup>3)</sup>	17	W
EAS	Single pulsed avalanche energy <sup>4)</sup>	1.2	mJ
T <sub>stg</sub> , T <sub>j</sub>	Operation and storage temperature	-55 to 150	°C
R <sub>θJC</sub>	Thermal resistance, junction-case	6.6	°C/W
R <sub>θJA</sub>	Thermal resistance, junction-ambient <sup>5)</sup>	62	°C/W



**Electrical Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	100	110	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>note3</sup>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.8	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance <sup>note2</sup>	$V_{GS} = 10V, I_D = 3A$	-	95	120	m $\Omega$
<b>Dynamic Characteristics</b> <sup>note4</sup>						
$C_{iss}$	Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	196	-	pF
$C_{oss}$	Output Capacitance		-	25.9	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	21.4	-	pF
$Q_g$	Total Gate Charge	$V_{DS} = 50V, I_D = 3A,$ $V_{GS} = 10V$	-	4.3	-	nC
$Q_{gs}$	Gate-Source Charge		-	3.5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	3.1	-	nC
<b>Switching Characteristics</b> <sup>note4</sup>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50V, I_{DS}=3A$ $R_G = 2\Omega, V_{GEN} = 10V$	-	14.7	-	ns
$t_r$	Turn-On Rise Time		-	3.5	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	20.9	-	ns
$t_f$	Turn-Off Fall Time		-	2.7	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current <sup>note2</sup>	-	-	12	-	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	12	-	A
$V_{SD}$	Drain to Source Diode Forward Voltage <sup>note3</sup>	$V_{GS} = 0V, I_S = 3A$	-	-	1.3	V
$t_{rr}$	Body Diode Reverse Recovery Time	$V_{GS} = 0V, I_F = 3A,$ $di/dt = 100A/\mu s$	-	32.1	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Time Charge		-	39.4	-	nC
$I_{rrm}$	Peak Reverse Recovery Current		-	2.1	-	A

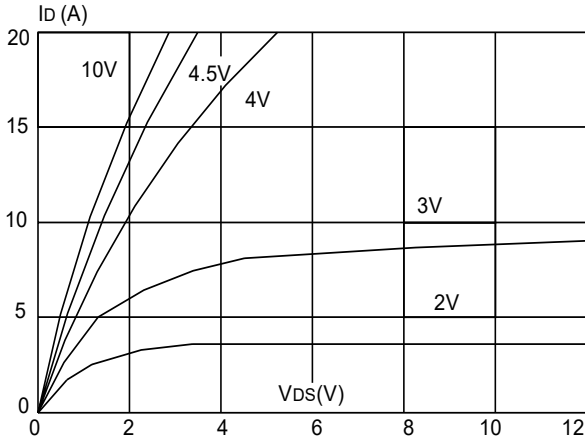
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5.  $V_{DD}=50V, R_G=50\Omega, L=0.3mH$ , starting  $T_J=25^\circ C$

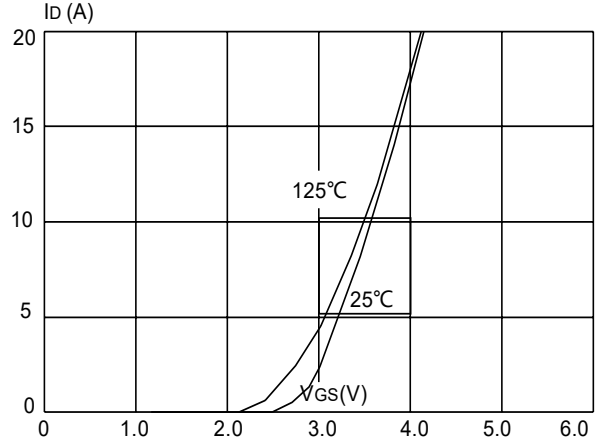


### Typical Performance Characteristics

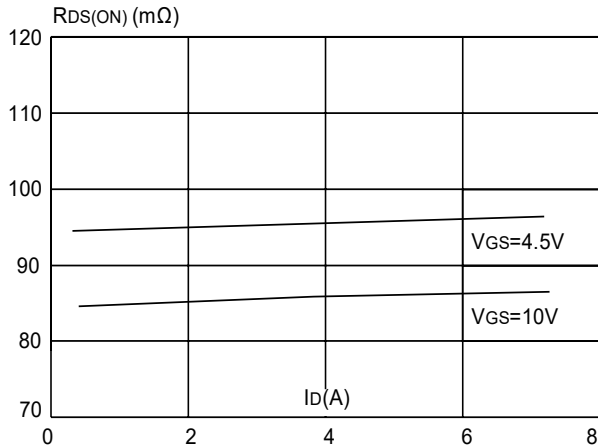
**Figure 1: Output Characteristics**



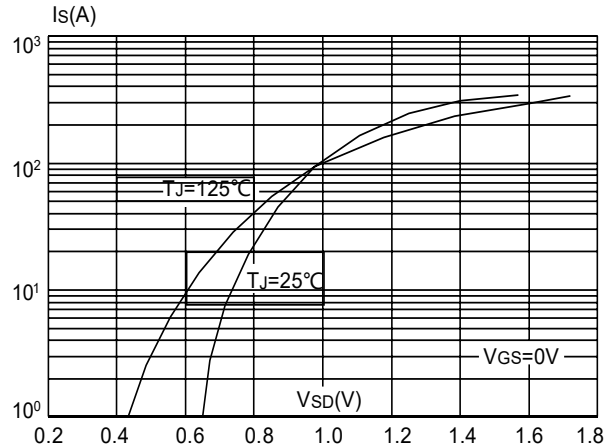
**Figure 2: Typical Transfer Characteristics**



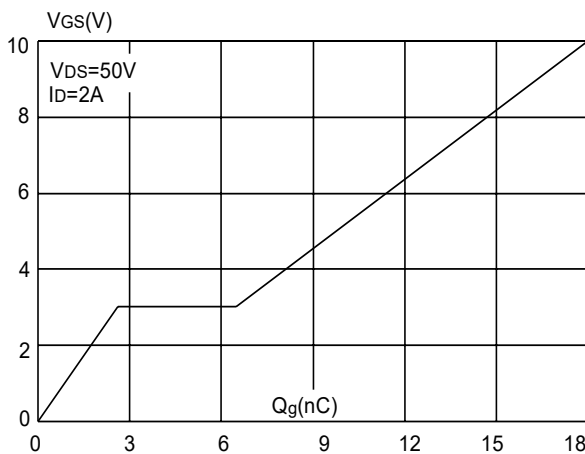
**Figure 3: On-resistance vs. Drain Current**



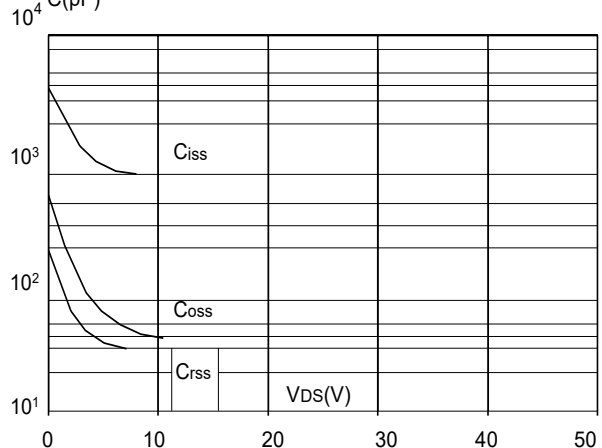
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

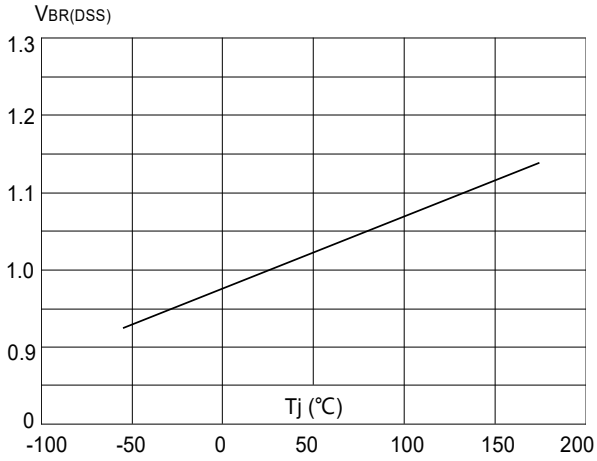


**Figure 6: Capacitance Characteristics**

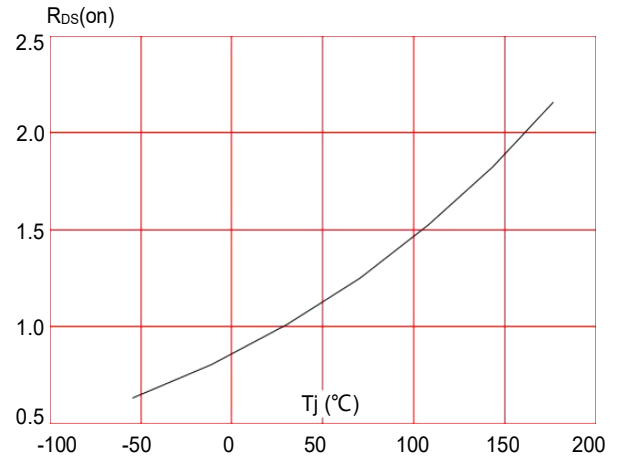




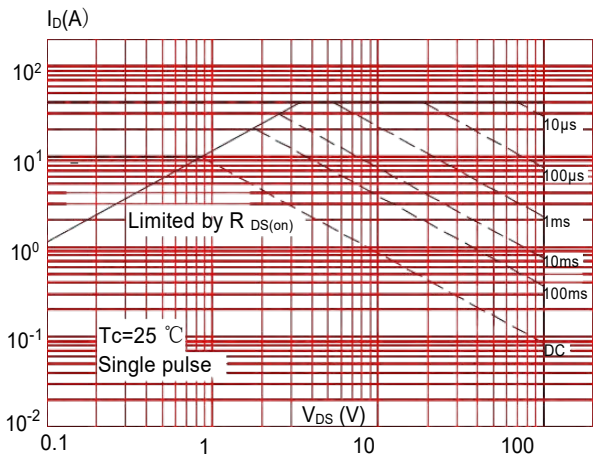
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



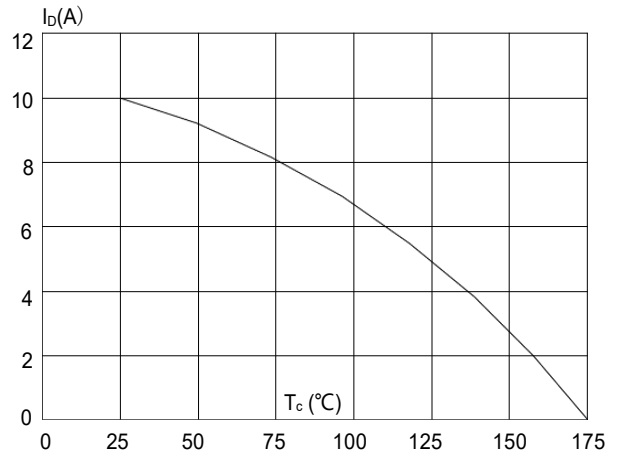
**Figure 8:** Normalized on Resistance vs. Junction Temperature



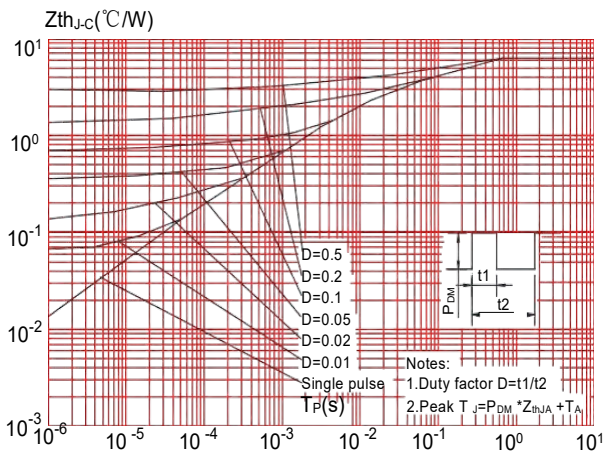
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

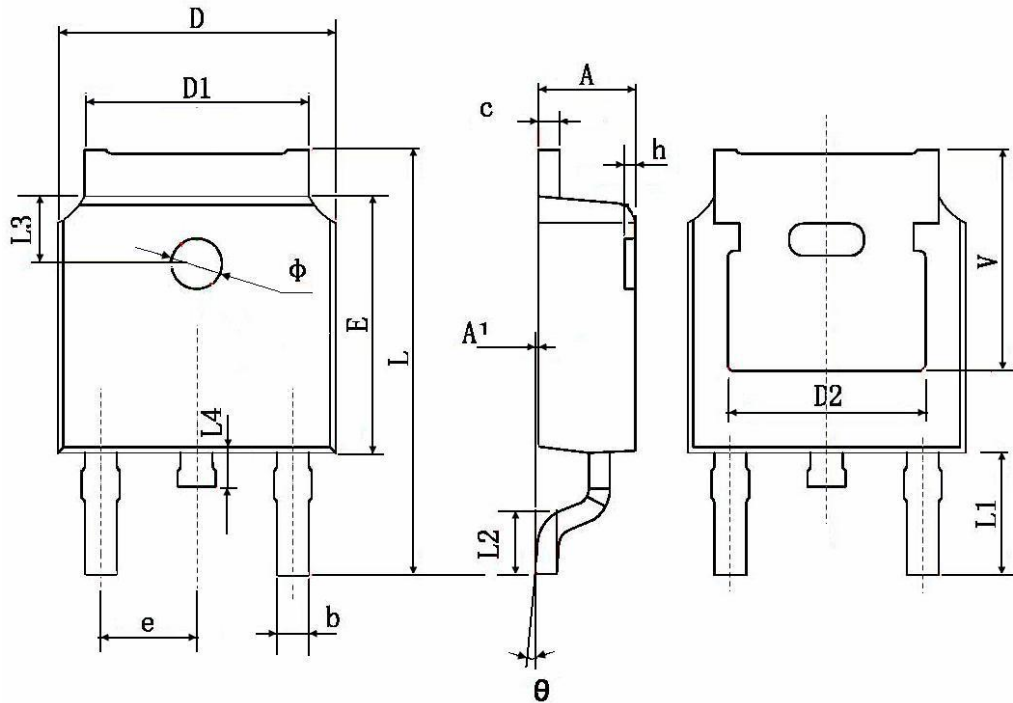


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





### TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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